

Saroj P Dash

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1404371/publications.pdf>

Version: 2024-02-01

43
papers

3,270
citations

218677

26
h-index

254184

43
g-index

43
all docs

43
docs citations

43
times ranked

4316
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical creation of spin polarization in silicon at room temperature. <i>Nature</i> , 2009, 462, 491-494.	27.8	565
2	Surface Energy Engineering for Tunable Wettability through Controlled Synthesis of MoS ₂ . <i>Nano Letters</i> , 2014, 14, 4314-4321.	9.1	258
3	Graphene spintronics: the European Flagship perspective. <i>2D Materials</i> , 2015, 2, 030202.	4.4	243
4	Electrical gate control of spin current in van der Waals heterostructures at room temperature. <i>Nature Communications</i> , 2017, 8, 16093.	12.8	224
5	Long distance spin communication in chemical vapour deposited graphene. <i>Nature Communications</i> , 2015, 6, 6766.	12.8	202
6	High-Performance Molybdenum Disulfide Field-Effect Transistors with Spin Tunnel Contacts. <i>ACS Nano</i> , 2014, 8, 476-482.	14.6	187
7	Enhanced Tunnel Spin Injection into Graphene using Chemical Vapor Deposited Hexagonal Boron Nitride. <i>Scientific Reports</i> , 2014, 4, 6146.	3.3	142
8	Room Temperature Electrical Detection of Spin Polarized Currents in Topological Insulators. <i>Nano Letters</i> , 2015, 15, 7976-7981.	9.1	141
9	Low Schottky Barrier Black Phosphorus Field-Effect Devices with Ferromagnetic Tunnel Contacts. <i>Small</i> , 2015, 11, 2209-2216.	10.0	111
10	Tunnel magnetoresistance with atomically thin two-dimensional hexagonal boron nitride barriers. <i>Nano Research</i> , 2015, 8, 1357-1364.	10.4	87
11	Unconventional Charge Spin Conversion in Weyl Semimetal WTe ₂ . <i>Advanced Materials</i> , 2020, 32, e2000818.	21.0	83
12	Magnetic proximity in a van der Waals heterostructure of magnetic insulator and graphene. <i>2D Materials</i> , 2020, 7, 015026.	4.4	80
13	Inversion of Spin Signal and Spin Filtering in Ferromagnet Hexagonal Boron Nitride-Graphene van der Waals Heterostructures. <i>Scientific Reports</i> , 2016, 6, 21168.	3.3	79
14	Observation of charge to spin conversion in Weyl semimetal WTe ₂ at room temperature. <i>Physical Review Research</i> , 2020, 2, .	10.3	78
15	Gate-tunable spin-galvanic effect in graphene-topological insulator van der Waals heterostructures at room temperature. <i>Nature Communications</i> , 2020, 11, 3657.	12.8	76
16	Efficient Spin Injection into Silicon and the Role of the Schottky Barrier. <i>Scientific Reports</i> , 2013, 3, 3196.	3.3	69
17	Tailoring emergent spin phenomena in Dirac material heterostructures. <i>Science Advances</i> , 2018, 4, eaat9349.	10.3	65
18	Spin-Polarized Tunneling through Chemical Vapor Deposited Multilayer Molybdenum Disulfide. <i>ACS Nano</i> , 2017, 11, 6389-6395.	14.6	53

#	ARTICLE	IF	CITATIONS
19	Spintronics with graphene-hexagonal boron nitride van der Waals heterostructures. Applied Physics Letters, 2014, 105, 212405.	3.3	43
20	Electrical Control of Hybrid Monolayer Tungsten Disulfideâ€“Plasmonic Nanoantenna Lightâ€“Matter States at Cryogenic and Room Temperatures. ACS Nano, 2020, 14, 1196-1206.	14.6	41
21	Oscillatory spin-polarized tunnelling from silicon quantum wells controlled by electric field. Nature Materials, 2010, 9, 133-138.	27.5	40
22	Challenges and opportunities in 2D heterostructures for electronic and optoelectronic devices. Science, 2022, 25, 103942.	4.1	38
23	Spin transport and precession in graphene measured by nonlocal and three-terminal methods. Applied Physics Letters, 2014, 104, .	3.3	36
24	Hall sensors batch-fabricated on all-CVD h-BN/graphene/h-BN heterostructures. Scientific Reports, 2017, 7, 15231.	3.3	33
25	Origin and evolution of surface spin current in topological insulators. Physical Review B, 2018, 97, .	3.2	33
26	Two-dimensional spintronic circuit architectures on large scale graphene. Carbon, 2020, 161, 892-899.	10.3	32
27	Electrically Controlled Spin Injection from Giant Rashba Spinâ€“Orbit Conductor BiTeBr. Nano Letters, 2020, 20, 4782-4791.	9.1	27
28	1D ferromagnetic edge contacts to 2D graphene/h-BN heterostructures. 2D Materials, 2018, 5, 014001.	4.4	26
29	Charge-spin conversion in layered semimetal TaAs and spin injection in van der Waals heterostructures. Physical Review Research, 2020, 2, .		
30	Gate-tunable Hall sensors on large area CVD graphene protected by h-BN with 1D edge contacts. Journal of Applied Physics, 2017, 122, .	2.5	20
31	All-electrical creation and control of spin-galvanic signal in graphene and molybdenum ditelluride heterostructures at room temperature. Communications Physics, 2021, 4, .	5.3	20
32	Salt-assisted growth of monolayer MoS2 for high-performance hysteresis-free field-effect transistor. Journal of Applied Physics, 2021, 129, .	2.5	19
33	Effect of high-k dielectric and ionic liquid gate on nanolayer black-phosphorus field effect transistors. Applied Physics Letters, 2015, 107, .	3.3	18
34	Manipulation of exciton and trion quasiparticles in monolayer WS2 via charge transfer. Applied Physics Letters, 2019, 115, .	3.3	14
35	Microwave Synthesized 2D Gold and Its 2D-2D Hybrids. Journal of Physical Chemistry Letters, 2022, 13, 6487-6495.	4.6	14
36	Electrically controlled spin-switch and evolution of Hanle spin precession in graphene. 2D Materials, 2019, 6, 035042.	4.4	12

#	ARTICLE	IF	CITATIONS
37	Robust Spin Interconnect with Isotropic Spin Dynamics in Chemical Vapor Deposited Graphene Layers and Boundaries. ACS Nano, 2020, 14, 15864-15873.	14.6	12
38	Thermal creation of electron spin polarization in n-type silicon. Applied Physics Letters, 2013, 103, .	3.3	10
39	Charge-spin conversion signal in WTe ₂ van der Waals hybrid devices with a geometrical design. Applied Physics Letters, 2020, 117, .	3.3	9
40	Observation of surface dominated topological transport in strained semimetallic ErPdB _i thin films. Applied Physics Letters, 2020, 117, 132406.	3.3	3
41	Initial stages of growth of iron on silicon for spin injection through Schottky barrier. Physica Status Solidi (B): Basic Research, 2011, 248, 2300-2304.	1.5	2
42	Surface dominated magnetotransport in Bi ₂ Te _{2.15} Se _{0.85} topological insulator. Journal of Applied Physics, 2018, 124, 214302.	2.5	1
43	Disorder is not always bad for charge-to-spin conversion in WTe ₂ . Matter, 2021, 4, 1440-1441.	10.0	1